

NCE N-Channel Super Trench II Power MOSFET

Description

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

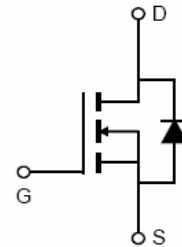
General Features

- $V_{DS} = 100V, I_D = 75A$
 $R_{DS(ON)} = 7.4m\Omega$, typical (TO-220) @ $V_{GS} = 10V$
- Excellent gate charge x $R_{DS(on)}$ product (FOM)
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating

100% UIS TESTED!

100% ΔV_{ds} TESTED!

TO-220



Schematic Diagram

Package Marking and Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|----------------|------------|----------------|-----------|------------|----------|
| NCEP080N10 | NCEP080N10 | TO-220 | - | - | - |

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|---|--------------------|------------|---------------|
| Drain-Source Voltage | V_{DS} | 100 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Drain Current-Continuous | I_D | 75 | A |
| Drain Current-Continuous($T_C = 100^\circ C$) | $I_D(100^\circ C)$ | 58 | A |
| Pulsed Drain Current | I_{DM} | 300 | A |
| Maximum Power Dissipation | P_D | 120 | W |
| Derating factor | | 0.8 | W/ $^\circ C$ |
| Single pulse avalanche energy ^(Note 4) | E_{AS} | 420 | mJ |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55 To 175 | $^\circ C$ |

Thermal Characteristic

| | | | |
|--------------------------------------|-----------------|------|--------------|
| Thermal Resistance, Junction-to-Case | $R_{\theta JC}$ | 1.25 | $^\circ C/W$ |
|--------------------------------------|-----------------|------|--------------|

Electrical Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|---|--------------|--|-----|------|-----------|------------|
| Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{GS}=0V, I_D=250\mu A$ | 100 | | - | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS}=100V, V_{GS}=0V$ | - | - | 1 | μA |
| Gate-Body Leakage Current | I_{GSS} | $V_{GS}=\pm 20V, V_{DS}=0V$ | - | - | ± 100 | nA |
| On Characteristics (Note 3) | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=250\mu A$ | 2.0 | 3.0 | 4.0 | V |
| Drain-Source On-State Resistance | $R_{DS(ON)}$ | $V_{GS}=10V, I_D=37.5A$ | - | 7.4 | 8.0 | m Ω |
| Forward Transconductance | g_{FS} | $V_{DS}=5V, I_D=37.5A$ | | 60 | - | S |
| Dynamic Characteristics (Note 3) | | | | | | |
| Input Capacitance | C_{iss} | $V_{DS}=50V, V_{GS}=0V,$ $F=1.0\text{MHz}$ | - | 3070 | - | pF |
| Output Capacitance | C_{oss} | | - | 290 | - | pF |
| Reverse Transfer Capacitance | C_{rss} | | - | 23 | - | pF |
| Switching Characteristics (Note 3) | | | | | | |
| Turn-on Delay Time | $t_{d(on)}$ | $V_{DD}=50V, I_D=37.5A$ $V_{GS}=10V, R_G=1.6\Omega$ | - | 15 | - | nS |
| Turn-on Rise Time | t_r | | - | 10 | - | nS |
| Turn-Off Delay Time | $t_{d(off)}$ | | - | 34 | - | nS |
| Turn-Off Fall Time | t_f | | - | 8 | - | nS |
| Total Gate Charge | Q_g | $V_{DS}=50V, I_D=37.5A,$ $V_{GS}=10V$ | - | 53 | - | nC |
| Gate-Source Charge | Q_{gs} | | - | 18 | - | nC |
| Gate-Drain Charge | Q_{gd} | | - | 16 | - | nC |
| Drain-Source Diode Characteristics | | | | | | |
| Diode Forward Voltage (Note 2) | V_{SD} | $V_{GS}=0V, I_S=37.5A$ | - | - | 1.2 | V |
| Diode Forward Current | I_S | | - | - | 75 | A |
| Reverse Recovery Time | t_{rr} | $T_J = 25^{\circ}\text{C}, I_F = 37.5A$ $di/dt = 100A/\mu s$ (Note 3) | - | 60 | - | nS |
| Reverse Recovery Charge | Q_{rr} | | - | 106 | - | nC |

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
3. Guaranteed by design, not subject to production
4. EAS condition : $T_J=25^{\circ}\text{C}, V_{DD}=50V, V_G=10V, L=0.25\text{mH}, R_g=25\Omega$

Typical Electrical and Thermal Characteristics

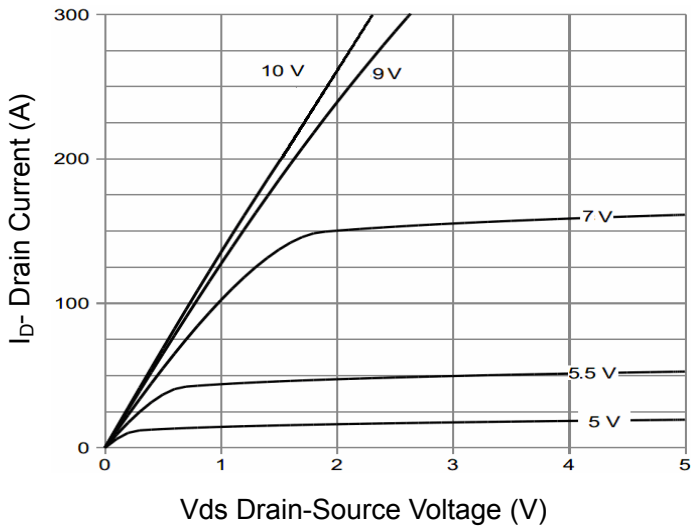


Figure 1 Output Characteristics

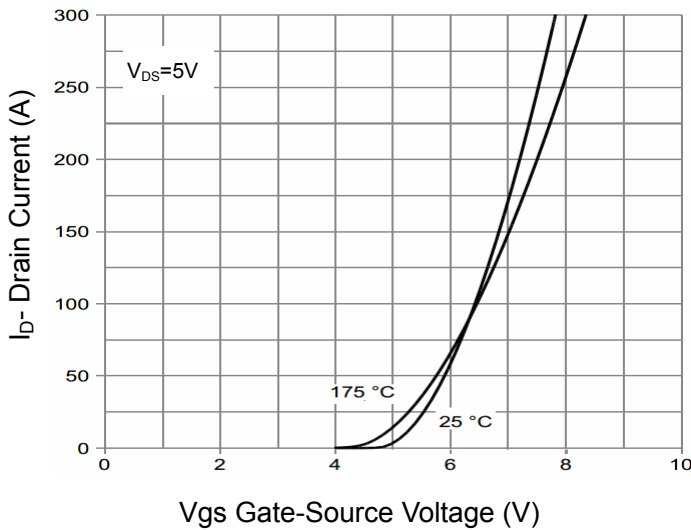


Figure 2 Transfer Characteristics

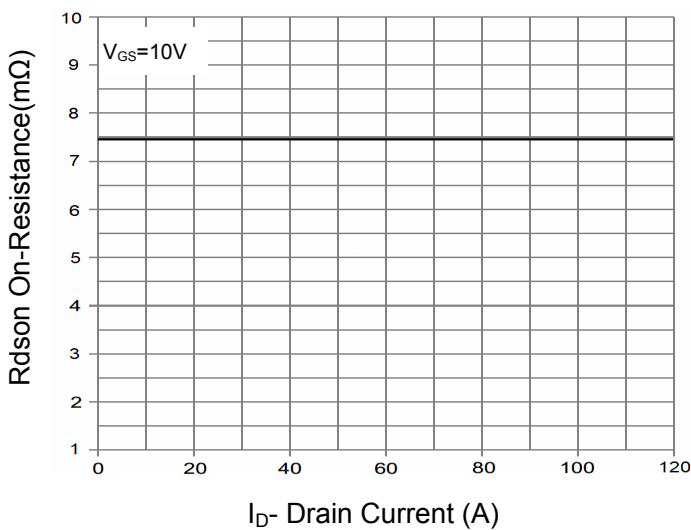


Figure 3 $R_{DS(on)}$ - Drain Current

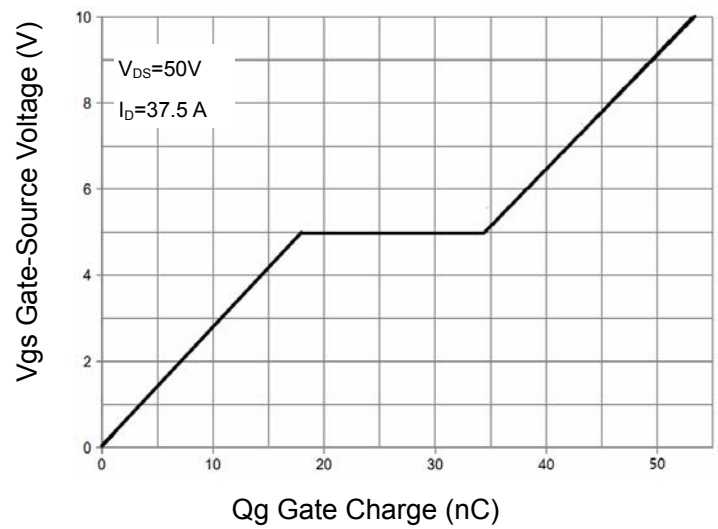


Figure 4 Gate Charge

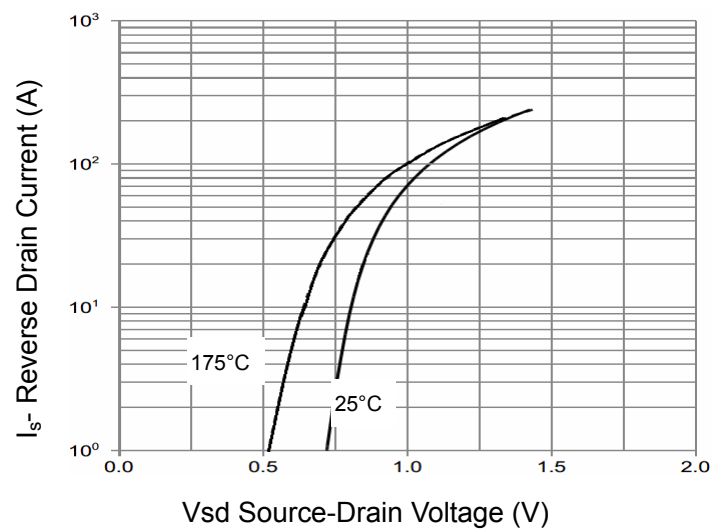


Figure 5 Source- Drain Diode Forward

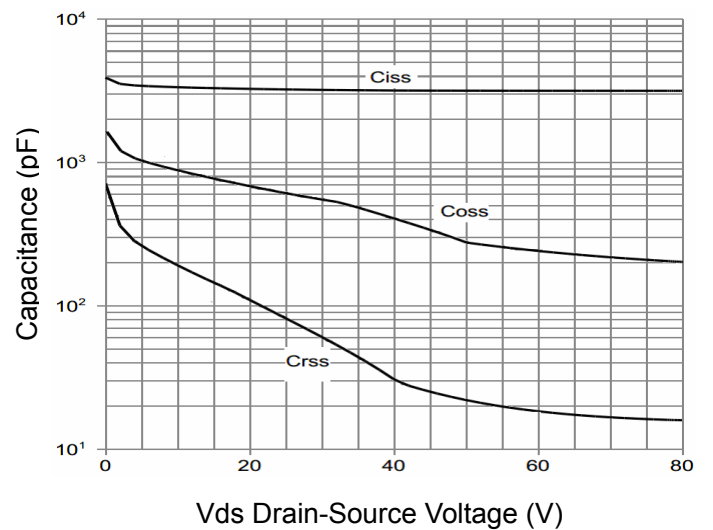
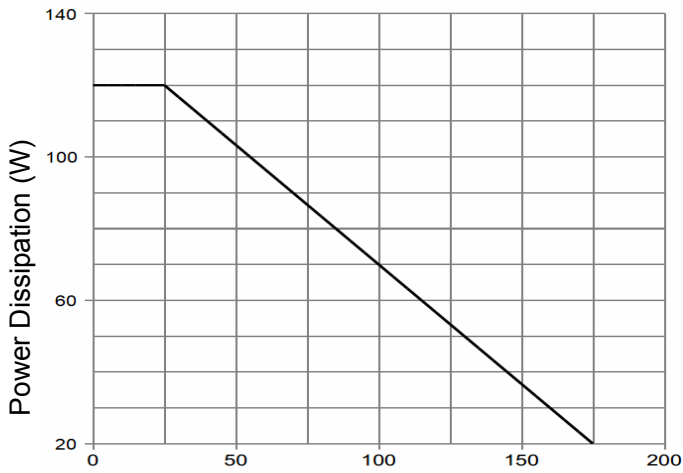
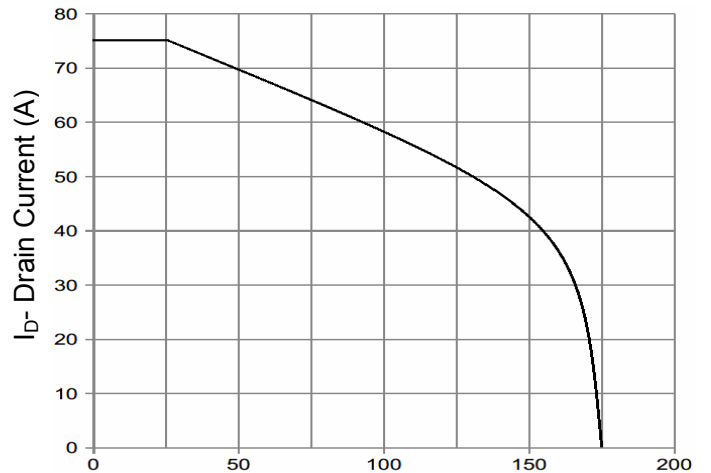


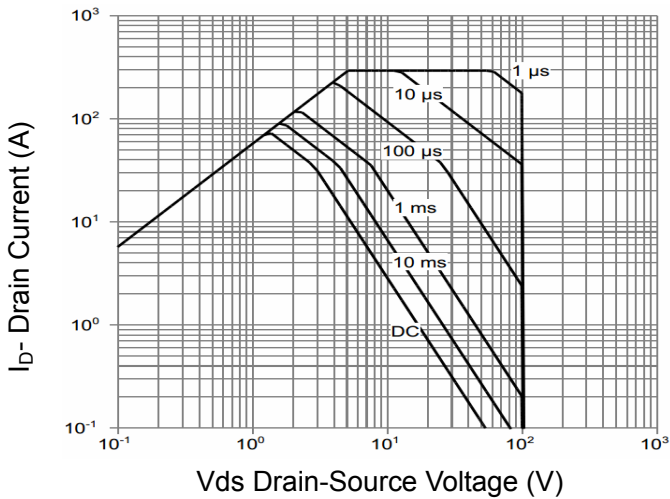
Figure 6 Capacitance vs V_{DS}



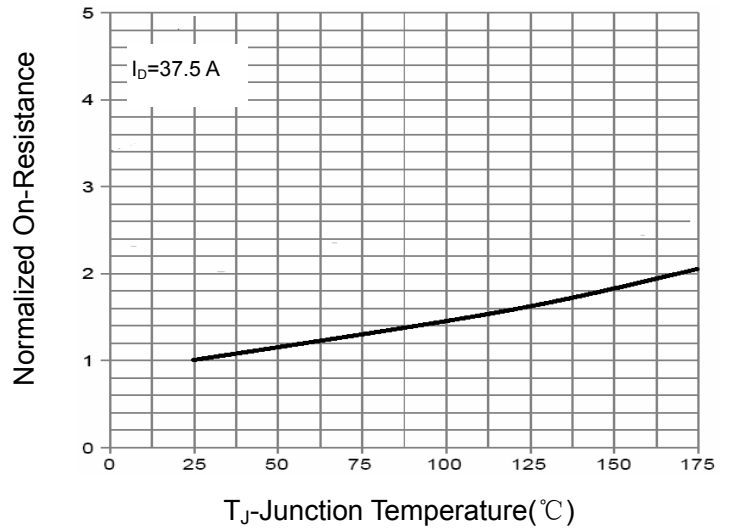
T_J-Junction Temperature(°C)
Figure 7 Power De-rating



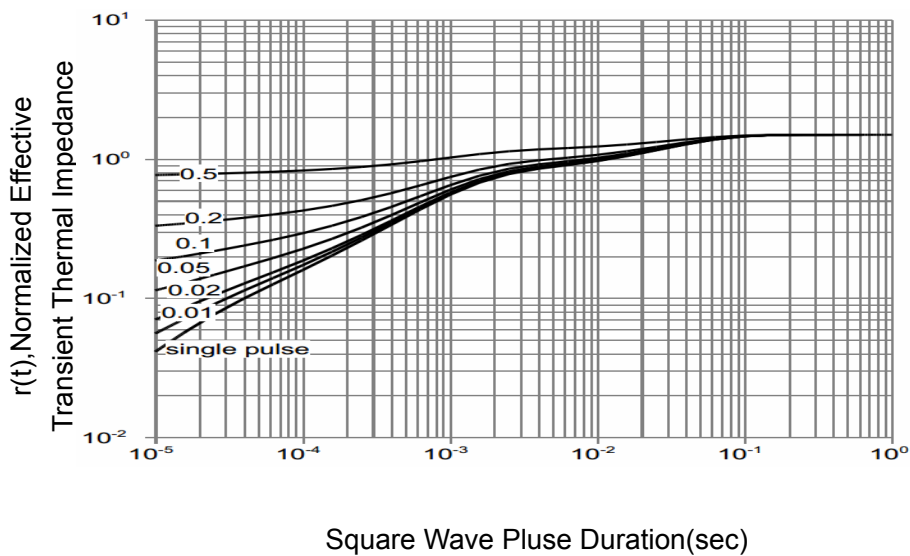
T_J-Junction Temperature (°C)
Figure 9 Current De-rating



V_{ds} Drain-Source Voltage (V)
Figure 8 Safe Operation Area

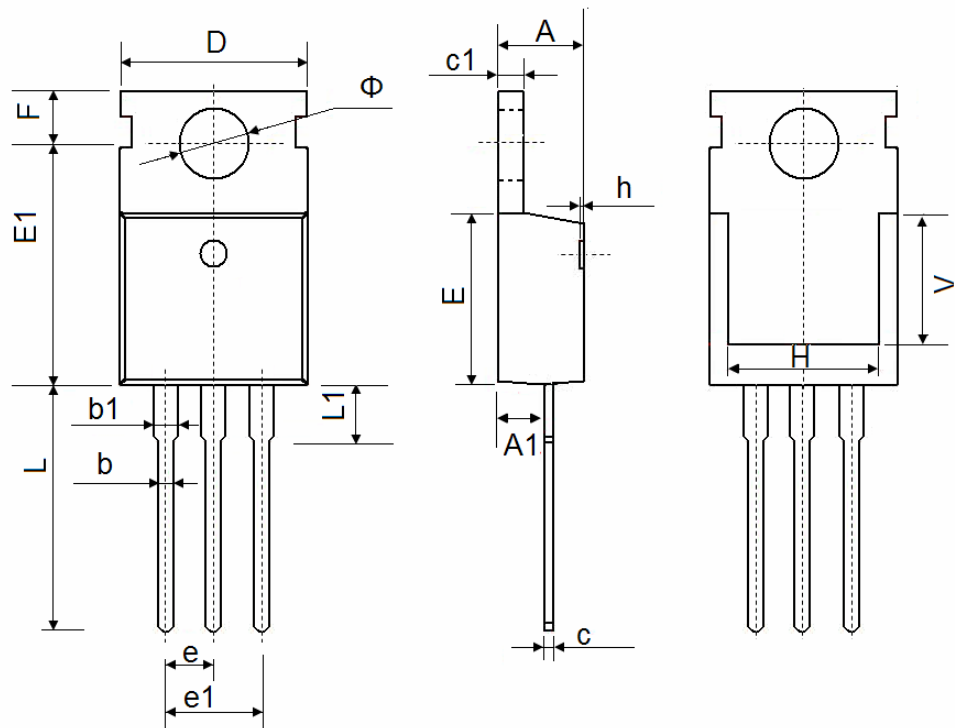


T_J-Junction Temperature(°C)
Figure 10 Rdson-Junction Temperature



Square Wave Pulse Duration(sec)
Figure 11 Normalized Maximum Transient Thermal Impedance

TO-220-3L Package Information



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|--------|----------------------|-------|
| | Min. | Max. | Min. | Max. |
| A | 4.400 | 4.600 | 0.173 | 0.181 |
| A1 | 2.250 | 2.550 | 0.089 | 0.100 |
| b | 0.710 | 0.910 | 0.028 | 0.036 |
| b1 | 1.170 | 1.370 | 0.046 | 0.054 |
| c | 0.330 | 0.650 | 0.013 | 0.026 |
| c1 | 1.200 | 1.400 | 0.047 | 0.055 |
| D | 9.910 | 10.250 | 0.390 | 0.404 |
| E | 8.9500 | 9.750 | 0.352 | 0.384 |
| E1 | 12.650 | 12.950 | 0.498 | 0.510 |
| e | 2.540 TYP. | | 0.100 TYP. | |
| e1 | 4.980 | 5.180 | 0.196 | 0.204 |
| F | 2.650 | 2.950 | 0.104 | 0.116 |
| H | 7.900 | 8.100 | 0.311 | 0.319 |
| h | 0.000 | 0.300 | 0.000 | 0.012 |
| L | 12.900 | 13.400 | 0.508 | 0.528 |
| L1 | 2.850 | 3.250 | 0.112 | 0.128 |
| V | 6.900 REF. | | 0.276 REF. | |
| Φ | 3.400 | 3.800 | 0.134 | 0.150 |

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